

Amendments to the Specification:

Please amend the title as follows:

FABRICATION METHOD OF SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE
INCLUDING USING PHOTOMASK PROPER FOR METHOD

Please amend paragraph 0154 as follows:

[0154] One example of the manufacturing step using such a conventional mask is illustrated in Figs. 10(a) to 10(d). First, a blocking film 5 made of chromium or the like is deposited over a mask substrate 3, followed by application thereto of a resist film 6 photosensitive to an electron beam (FIG. 710(a)). The light blocking film 5 is not limited to chromium, but various films can be employed. For example, refractory metals, such as tungsten (W), molybdenum (Mo), tantalum (Ta) and titanium (Ti), refractory metal nitrides, such as tungsten nitride (WN), and refractory metal silicides (compounds), such as tungsten silicide (WSix) and molybdenum silicide (MoSix), and a laminate film thereof may be used. In the case of a resist mask, which will be described later, a light blocking pattern is preferably made of a metal having a high peeling resistance and abrasion resistance, because there is a possibility of washing and then using the mask substrate again after removal of the light blocking pattern made of a resist film. Refractory metals, such as tungsten, have a high oxidation resistance, abrasion resistance and peeling resistance, so that they are suited as a material for the light blocking pattern made of a metal. Then, resist patterns 6a are formed by exposure of the resist film 6 to electron beams EB having predetermined pattern data, and then, development occurs (FIG. 710(b)). Using these resist patterns 6a as an etching mask, the light blocking film 5 is etched to form light blocking patterns 5a, 5b (FIG. 710(c)). The resist patterns 6a

photosensitive to electron beams are then removed in the end, whereby a conventional mask M is fabricated (FIG. 7(b)10(d)). Such a conventional mask has a high durability and high reliability and can therefore be utilized for a great deal of exposure treatment, so that it is suited for use as a mask for mass production of a semiconductor integrated circuit device.

Please amend the abstract as shown on the next page:

A method of ~~fabrication method of~~fabricating a semiconductor integrated circuit device provides for the use of a photomask having light blocking patterns made of a metal and another photomask having light blocking patterns made of a resist film during exposure treatment, the type of photomask being selected depending on the fabrication step of the semiconductor integrated circuit device. With such a method, the productivity of the semiconductor integrated circuit device can be improved.